

# 1.2V Drive Nch MOSFET

# RU1C002UN

#### Structure

Silicon N-channel MOSFET

#### ● Features

- 1) Low on-resistance.
- 2) Low voltage drive(1.2V drive).

## Application

Switching

# Packaging specifications

	Package	Taping
Type	Code	TCL
	Basic ordering unit (pieces)	3000
RU1C002L	0	

## ● Absolute maximum ratings (Ta = 25°C)

Parame	Symbol	Limits	Unit	
Drain-source voltage		$V_{DSS}$	20	V
Gate-source voltage		$V_{GSS}$	±8	V
Drain current	Continuous	$I_D$	±200	mA
	Pulsed	I <sub>DP</sub> *1	±400	mA
Power dissipation		P <sub>D</sub> *2	150	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

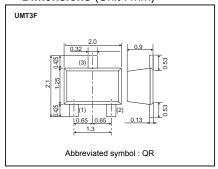
<sup>\*1</sup> Pw≤10µs, Duty cycle≤1%

# ● Thermal resistance

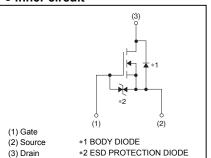
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	833	°C/W

<sup>\*</sup> Each terminal mounted on a reference land.

#### • Dimensions (Unit : mm)



## • Inner circuit



<sup>\*2</sup> Each terminal mounted on a reference land.

# ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	1	-	±10	μA	$V_{GS}=\pm 8V$ , $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	20	-	-	٧	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	1	-	1	μA	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.3	-	1.0	٧	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA
		1	0.8	1.2		I <sub>D</sub> =200mA, V <sub>GS</sub> =2.5V
Static drain-source on-state	* R	1	1.0	1.4	0	I <sub>D</sub> =200mA, V <sub>GS</sub> =1.8V
resistance	R <sub>DS (on)</sub>	-	1.2	2.4	Ω	I <sub>D</sub> =40mA, V <sub>GS</sub> =1.5V
		-	1.6	4.8		I <sub>D</sub> =20mA, V <sub>GS</sub> =1.2V
Forward transfer admittance	IY <sub>fs</sub> I*	400	-	-	mS	V <sub>DS</sub> =10V, I <sub>D</sub> =200mA
Input capacitance	C <sub>iss</sub>	1	25	-	pF	V <sub>DS</sub> =10V
Output capacitance	C <sub>oss</sub>	1	10	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	-	10	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	-	5	-	ns	V <sub>DD</sub> ≒10V, I <sub>D</sub> =150mA
Rise time	t <sub>r</sub> *	-	10	-	ns	V <sub>GS</sub> =4.0V
Turn-off delay time	t <sub>d(off)</sub> *	-	15	-	ns	$R_L$ =68 $\Omega$
Fall time	t <sub>f</sub> *	-	10	-	ns	$R_G$ =10 $\Omega$

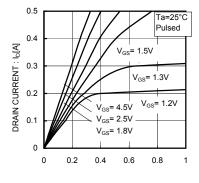
<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain)

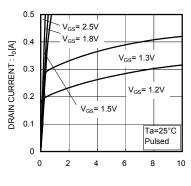
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V <sub>SD</sub> *	-	-	1.2	V	I <sub>s</sub> =100mA, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

#### Electrical characteristics

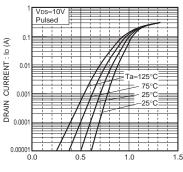


DRAIN-SOURCE VOLTAGE :  $V_{DS}[V]$ Fig.1 Typical Output Characteristics( I )



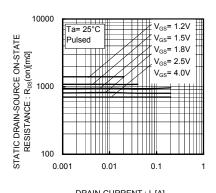
DRAIN-SOURCE VOLTAGE : V<sub>DS</sub>[V]





GATE-SOURCE VOLTAGE: VGs (V)

Fig.3 Typical transfer characteristics



DRAIN-CURRENT : I<sub>D</sub>[A]

Fig.4 Static Drain-Source On-State
Resistance vs. Drain Current( I )

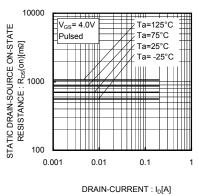


Fig.5 Static Drain-Source On-State
Resistance vs. Drain Current( II )

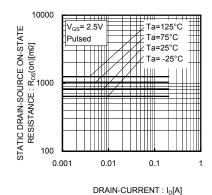


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current( II )

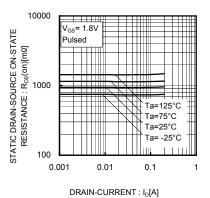


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

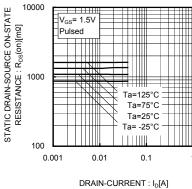


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(IV)

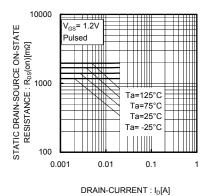


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current( V )

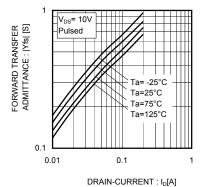


Fig.10 Forward Transfer Admittance vs. Drain Current

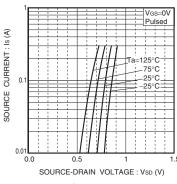


Fig.11 Source current vs.

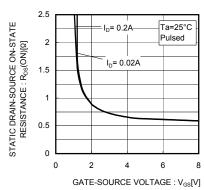


Fig.12 Static Drain-Source On-State
Resistance vs. Gate Source Voltage

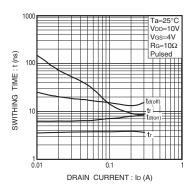


Fig.13 Switching characteristics

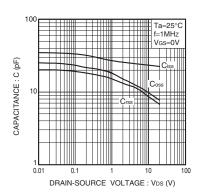


Fig.14 Typical capacitance vs. drain-source voltage

## Measurement circuits

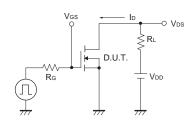


Fig.1-1 Switching Time Measurement Circuit

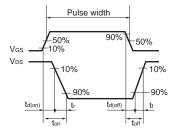


Fig.1-2 Switching Waveforms

#### Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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